



PNP Silicon Transistor

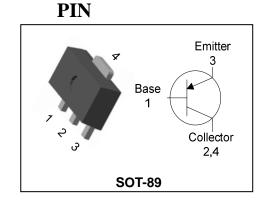
Description

• Medium power amplifier

Features

- P_C(Collector power dissipation)
 - =1W(Ceramic substate of 250 m²×0.8t used)
- Low collector saturation voltage : V_{CE(sat)}=-0.2V(Typ.)
- Complementary pair with STD1664

Ordering Information



| Type NO. | Marking | Package Code | |
|---|-----------|--------------|--|
| STB1132 | A1 YWW | SOT-89 | |
| A1: DEVICE CODE, YWW(Y: Year code, WW: Weekly code) | | | |

Absolute maximum ratings

(Ta=25°C)

| Characteristic | Symbol | Ratings | Unit |
|-----------------------------|------------------|---------|------|
| Collector-Base voltage | V_{CBO} | -40 | V |
| Collector-Emitter voltage | $V_{\sf CEO}$ | -32 | V |
| Emitter-Base voltage | V_{EBO} | -5 | V |
| Collector current | I _C | -1 | А |
| Callagtar mayor dissination | P _C | 0.5 | \A/ |
| Collector power dissipation | P _C * | 1 | W |
| Junction temperature | T _J | 150 | °C |
| Storage temperature | T _{stg} | -55~150 | °C |

^{*:} When mounted on ceramic substrate(250 mm²×0.8t)

Electrical Characteristics

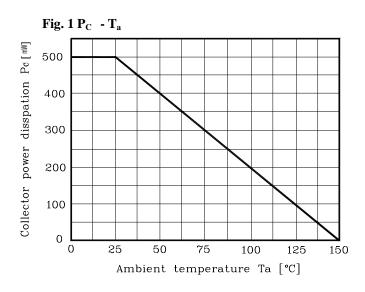
(Ta=25°C)

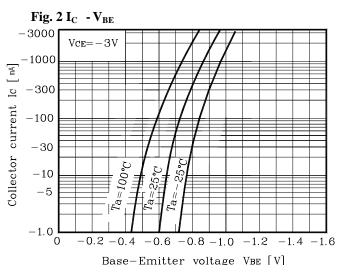
| Characteristic | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|--------------------------------------|----------------------|---|------|------|------|------|
| Collector-Base breakdown voltage | BV _{CBO} | $I_{C} = -50 \mu A, I_{E} = 0$ | -40 | - | - | V |
| Collector-Emitter breakdown voltage | BV _{CEO} | $I_C=-1$ MA, $I_B=0$ | -32 | 1 | - | V |
| Emitter-Base breakdown voltage | BV _{EBO} | $I_E = -50 \mu A, I_C = 0$ | -5 | 1 | - | V |
| Collector cut-off current | I _{CBO} | $V_{CB} = -20V, I_{E} = 0$ | - | - | -0.1 | μA |
| Collector cut-off current | I _{CES} | $V_{CE} = -30V$, $I_{C} = 0$ | - | - | -0.1 | μA |
| Emitter cut-off current | I _{EBO} | V_{EB} =-4 V , I_{C} =0 | - | - | -0.1 | μA |
| DC current gain | h _{FE} * | $V_{CE} = -3V$, $I_{C} = -0.1A$ | 100 | - | 320 | - |
| Collector-Emitter saturation voltage | V _{CE(sat)} | $I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$ | - | -0.2 | -0.8 | V |
| Transition frequency | f _T | V_{CE} =-5V, I_{C} =-50 mA, f =30 MHz | - | 150 | - | MHz |
| Collector output capacitance | C _{ob} | V_{CB} =-10V, I_{E} =0, f =1 MHz | - | 20 | 30 | pF |

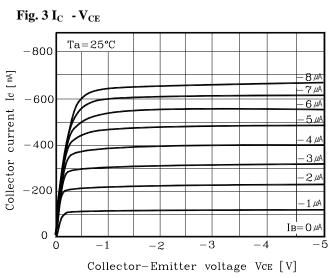
^{* :} h_{FE} rank / O : 100 ~ 200, Y : 160 ~ 320

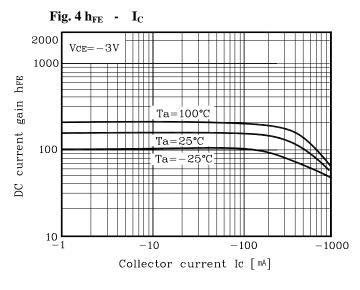
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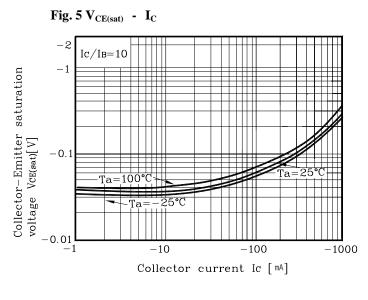
Electrical Characteristic Curves

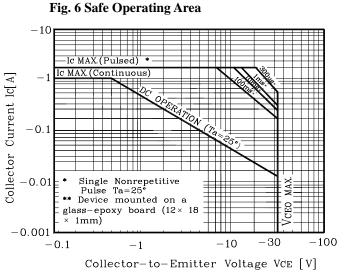






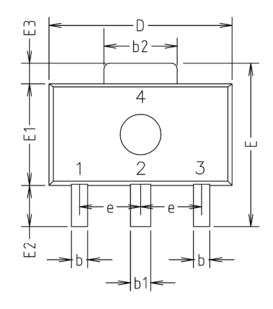


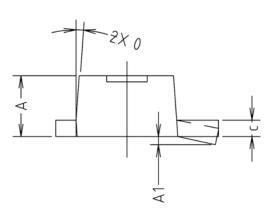




KSD-T5B021-001 2

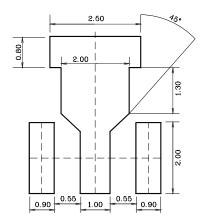
Outline Dimension(mm)





| | MILLIMETERS | | | |
|--------|-------------|-----------|---------|------|
| SYMBOL | MINIMUM | NOMINAL | MAXIMUM | NOTE |
| Α | 1.40 | 1.50 | 1.60 | |
| A1 | 0.00 | _ | 0.10 | |
| b | 0.38 | 0.42 | 0.48 | |
| b1 | 0.48 | 0.52 | 0.58 | |
| b2 | 1.79 | 1.82 | 1.87 | |
| С | 0.40 | 0.42 | 0.46 | |
| D | 4.40 | 4.50 | 4.70 | |
| Ε | 3.70 | 4.00 | 4.30 | |
| E1 | 2.40 | 2.50 | 2.70 | |
| E2 | 0.80 | 1.00 | 1.20 | |
| E3 | 0.40 | 0.50 | 0.60 | |
| е | | 1.50 TYP. | | |
| 0 | | 4° TYP. | | |

*Recommend PCB solder land [Unit: mm]



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KSD-T5B021-001